

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property  
Organization  
International Bureau

(43) International Publication Date  
25 June 2020 (25.06.2020)



(10) International Publication Number  
**WO 2020/131155 A1**

(51) International Patent Classification:

C09G 1/02 (2006.01) C23F 3/00 (2006.01)  
C09G 1/04 (2006.01)

(21) International Application Number:

PCT/US2019/029138

(22) International Filing Date:

25 April 2019 (25.04.2019)

(25) Filing Language:

English

(26) Publication Language:

English

(30) Priority Data:

62/781,648 19 December 2018 (19.12.2018) US  
16/356,685 18 March 2019 (18.03.2019) US

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(81) Designated States (unless otherwise indicated, for every kind of national protection available):

AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DJ, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IR, IS, JO, JP, KE, KG, KH, KN, KP, KR, KW, KZ, LA, LC, LK, LR, LS, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SA, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States (unless otherwise indicated, for every kind of regional protection available):

ARIPO (BW, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SD, SL, ST, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, KM, ML, MR, NE, SN, TD, TG).

Published:

— with international search report (Art. 21(3))

(54) Title: POLISHING COMPOSITIONS AND METHODS OF USING SAME

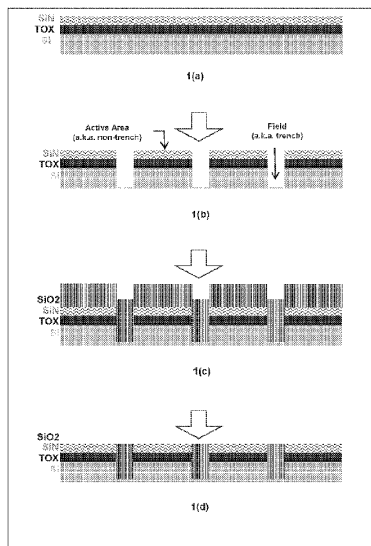


Figure 1.

(57) Abstract: This disclosure relates to a polishing composition that includes at least one abrasive; at least one nitride removal rate reducing agent, an acid or a base; and water. The at least one nitride removal rate reduce agent can include a hydrophobic portion and a hydrophilic portion; in which the hydrophobic portion includes a C<sub>12</sub> to C<sub>40</sub> hydrocarbon group and is separated by zero to ten alkylene oxide groups from the hydrophilic portion. The polishing composition has a pH of about 2 to about 6.5, and can have a ratio of a removal rate for a silicon oxide to a removal rate for a silicon nitride of at least about 3:1 when polishing a patterned wafer comprising at least silicon nitride patterns overlaid with at least silicon oxide.

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